

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (currently amended) A method of producing a glass substrate for a mask blank, said mask blank being for use in a transfer mask which is for use with F2 excimer laser light or EUV (extreme ultra violet) light as an exposure light source, the method comprising:

a profile measuring step of measuring a convex/concave profile of a surface of the glass substrate for a mask blank;

a flatness control step of controlling a flatness of the surface of the glass substrate to a value not greater than a ~~predetermined reference value determined depending upon a required flatness required to the glass substrate~~ flatness required in lithography using the F2 excimer laser light or the EUV light as the exposure light source by specifying the degree of convexity of a convex portion present on the surface of the glass substrate with reference to a result of measurement obtained in the profile measuring step and by executing local machining upon the convex portion under a machining condition depending upon the degree of convexity; and

a non-contact polishing step of polishing, after the local machining of the flatness control step, the surface of the glass substrate subjected to the local machining by the action of a machining liquid interposed between the surface of the glass substrate and a surface of a polishing tool without direct contact therebetween;

the local machining being carried out by plasma etching, a gas cluster ion beam, or MRF (Magnetorheological Finishing);

the non-contact polishing step being carried out by at least one of float polishing, elastic emission machining (EEM), and hydroplane polishing.

2. (currently amended) A method ~~according to claim 1, wherein~~ of producing a glass substrate for a mask blank, the method comprising:

a profile measuring step of measuring a convex/concave profile of a surface of the glass substrate for a mask blank;

a flatness control step of controlling a flatness of the surface of the glass substrate to a value not greater than 0.25 μm by specifying the degree of convexity of a convex portion present on the surface of the glass substrate with reference to a result of measurement obtained in the profile measuring step and by executing local machining upon the convex portion under a machining condition depending upon the degree of convexity; and

a non-contact polishing step of polishing, after the local machining of the flatness control step, the surface of the glass substrate subjected to the local machining by the action of a machining liquid interposed between the surface of the glass substrate and a surface of a polishing tool without direct contact therebetween;

the local machining being carried out by at least one of plasma etching, a gas cluster ion beam, or MRF (Magnetorheological Finishing);

the non-contact polishing step is being carried out by at least one of float polishing, elastic emission machining (EEM), and hydroplane polishing.

3. (currently amended) A method according to claim 1 ~~or~~ 2, wherein:

the machining liquid used in the non-contact polishing step comprises:

an aqueous solution selected from water, an acidic aqueous solution, and an alkaline aqueous solution; or

a mixture of the aqueous solution and at least one kind of fine powder particles selected from colloidal silica, cerium oxide, zirconium oxide, and aluminum oxide.

4. (canceled).

5. (currently amended) A method according to claim 1, wherein the reference ~~value~~ flatness is not greater than 0.25 μm .

6. (previously amended) A method of producing a mask blank, the method comprising the steps of preparing the glass substrate obtained by the method according to claim 1, and forming a thin film as a transferred pattern on the glass substrate.

7. (original) A method of producing a transfer mask, the method comprising the steps of preparing the mask blank obtained by the method according to claim 6 and patterning the thin film of the mask blank to form a thin film pattern on the glass substrate.

8. (original) A method of producing a semiconductor device, the method comprising the steps of preparing the transfer mask obtained by the method according to claim 7 and transferring the thin film pattern of the transfer mask onto a semiconductor substrate by lithography.

9. (new) A method of producing a reflective mask blank, the method comprising the steps of preparing the glass substrate obtained by the method according to claim 1, forming a reflective multilayer film on the glass substrate, and forming a light absorber film on the reflective multilayer film to obtain the reflective mask blank.

10. (new) A method according to claim 2, wherein:
the machining liquid used in the non-contact polishing step comprises:
an aqueous solution selected from water, an acidic aqueous solution, and an alkaline aqueous solution; or
a mixture of the aqueous solution and at least one kind of fine powder particles selected from colloidal silica, cerium oxide, zirconium oxide, and aluminum oxide.

11. (new) A method of producing a mask blank, the method comprising the steps of preparing the glass substrate obtained by the method according to claim 2, and forming a thin film as a transferred pattern on the glass substrate.

12. (new) A method of producing a transfer mask, the method comprising the steps of preparing the mask blank obtained by the method according to claim 11 and patterning the thin film of the mask blank to form a thin film pattern on the glass substrate.

13. (new) A method of producing a semiconductor device, the method comprising the steps of preparing the transfer mask obtained by the method according to claim 12 and transferring the thin film pattern of the transfer mask onto a semiconductor substrate by lithography.

14. (new) A method of producing a reflective mask blank, the method comprising the steps of preparing the glass substrate obtained by the method according to claim 2, forming a

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reflective multilayer film on the glass substrate, and forming a light absorber film on the reflective multilayer film to obtain the reflective mask blank.